

# BCR20AM-12LB

### Triac

Medium Power Use

(The product guaranteed maximum junction temperature of 150°C)

REJ03G0458-0300 Rev.3.00 Nov 30, 2007

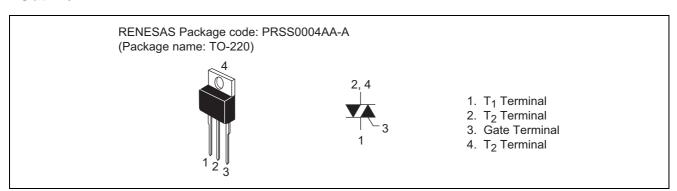
#### **Features**

•  $I_{FGTI}$ ,  $I_{RGTI}$ ,  $I_{RGT III}$ : 30 mA (20 mA)<sup>Note6</sup>

Non-Insulated Type

Planar Passivation Type

#### **Outline**



# **Applications**

Vacuum cleaner, electric heater, light dimmer, copying machine, and controller for other motor and heater

# Warning

- 1. Refer to the recommended circuit values around the triac before using.
- 2. Be sure to exchange the specification before using. Otherwise, general triacs with the maximum junction temperature of 125°C will be supplied.

### **Maximum Ratings**

Parameter	Symbol	Voltage class	Unit	
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Repetitive peak off-state voltage <sup>Note1</sup>	$V_{DRM}$	600	V	
Non-repetitive peak off-state voltage <sup>Note1</sup>	$V_{DSM}$	720	V	

# BCR20AM-12LB (The product guaranteed maximum junction temperature of 150°C)

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I <sub>T (RMS)</sub>	20	А	Commercial frequency, sine full wave 360° conduction, Tc = 134°C <sup>Note3</sup>
Surge on-state current	I <sub>TSM</sub>	200	А	60Hz sinewave 1 full cycle, peak value, non-repetitive
I <sup>2</sup> t for fusing	l <sup>2</sup> t	167	A <sup>2</sup> s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	$P_{GM}$	5	W	
Average gate power dissipation	P <sub>G (AV)</sub>	0.5	W	
Peak gate voltage	$V_{GM}$	10	V	
Peak gate current	I <sub>GM</sub>	2	Α	
Junction temperature	Tj	- 40 to +150	°C	
Storage temperature	Tstg	- 40 to +150	°C	
Mass	_	2.0	g	Typical value

Notes: 1. Gate open.

### **Electrical Characteristics**

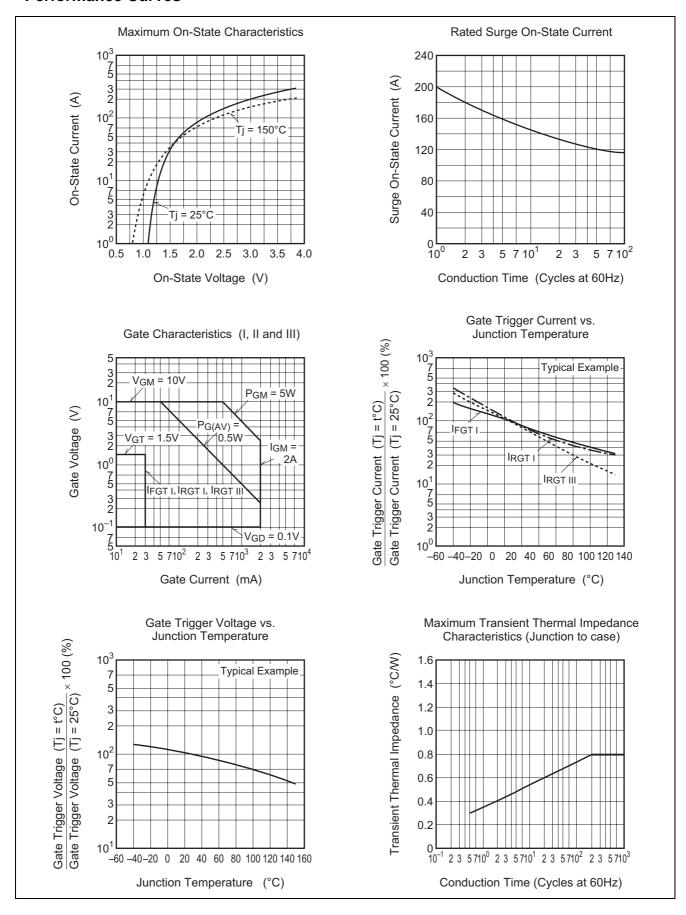
Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state current		I <sub>DRM</sub>	_	_	2.0/3.0	mA	Tj = 125°C/150°C, V <sub>DRM</sub> applied
On-state voltage		$V_{TM}$	_	_	1.5	V	Tc = 25°C, I <sub>TM</sub> = 30 A, Instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	I	$V_{FGTI}$	_	_	1.5	V	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,
	II	$V_{RGTI}$	_	_	1.5	V	$R_G = 330 \Omega$
	III	$V_{RGTIII}$	_	_	1.5	V	
Gate trigger current <sup>Note2</sup>	I	$I_{FGTI}$	_	_	30 <sup>Note6</sup>	mA	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,
	II	$I_{RGTI}$	_	_	30 <sup>Note6</sup>	mA	$R_G = 330 \Omega$
	III	$I_{RGT_{III}}$	_	_	30 <sup>Note6</sup>	mA	
Gate non-trigger voltage		$V_{GD}$	0.2/0.1	_	_	V	$Tj = 125^{\circ}C/150^{\circ}C, V_D = 1/2 V_{DRM}$
Thermal resistance		R <sub>th (j-c)</sub>	_	_	0.8	°C/W	Junction to case Note3 Note4
Critical-rate of rise of off-state commutating voltage <sup>Note5</sup>		(dv/dt)c	10/1	_	_	V/μs	Tj = 125°C/150°C

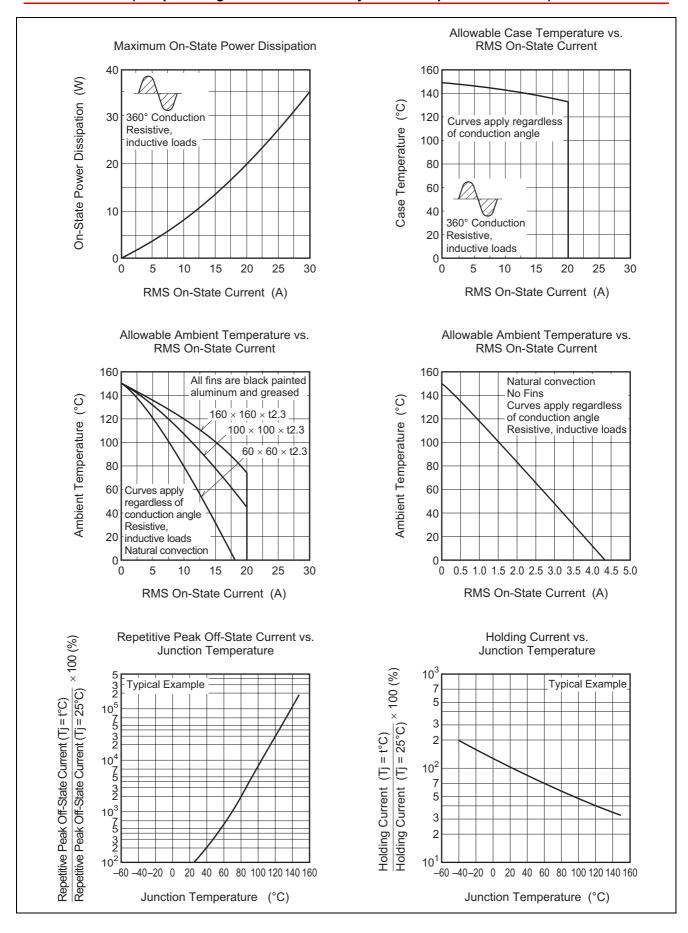
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

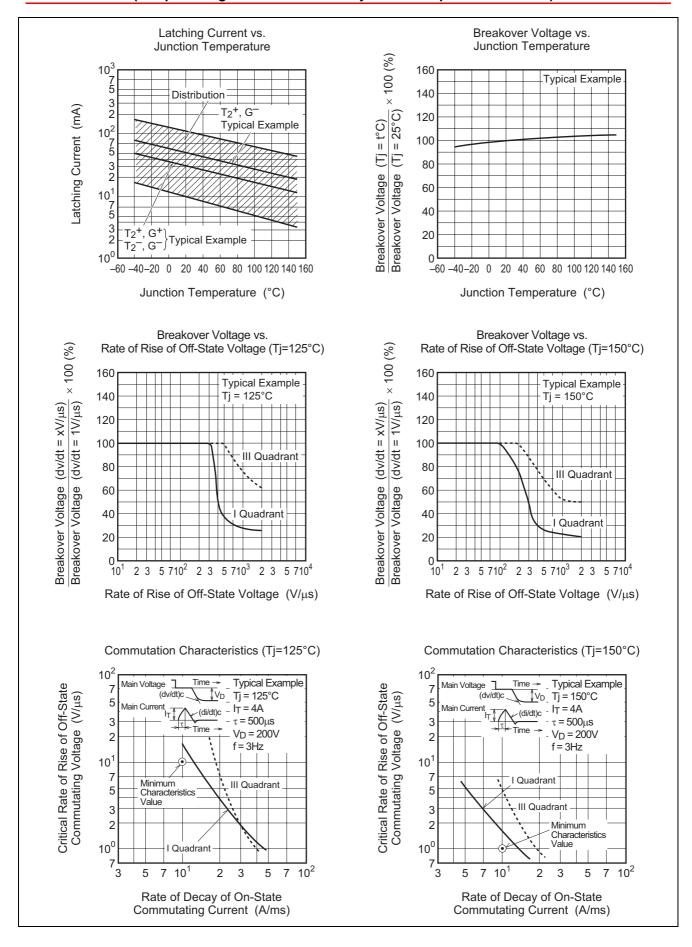
- 3. Case temperature is measured at the  $T_2$  tab 1.5 mm away from the molded case.
- 4. The contact thermal resistance  $R_{th\ (c-f)}$  in case of greasing is 1.0°C/W.
- 5. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.
- 6. High sensitivity ( $I_{GT} \le 20$  mA) is also available. ( $I_{GT}$  item: 1)

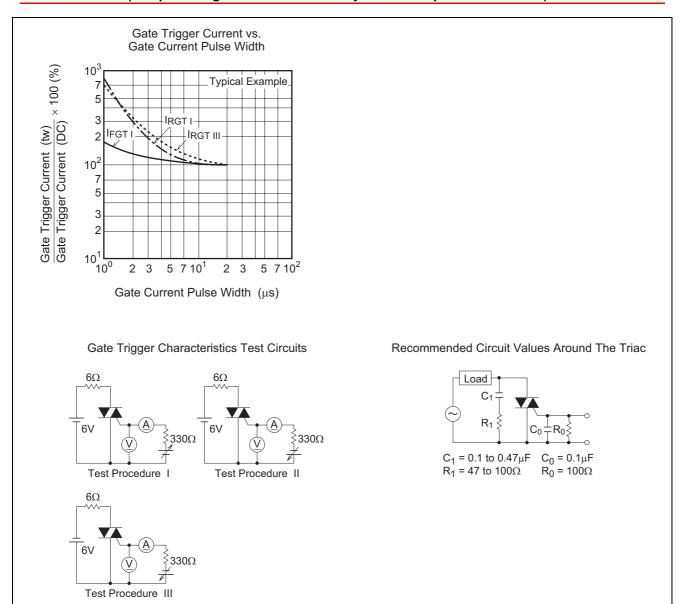
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature Tj = 125°C/150°C	Supply Voltage  → Time
2. Rate of decay of on-state commutating current (di/dt)c = -10 A/ms	Main Current (di/dt)c  → Time
3. Peak off-state voltage $V_D = 400 \text{ V}$	Main Voltage — Time (dv/dt)c

#### **Performance Curves**

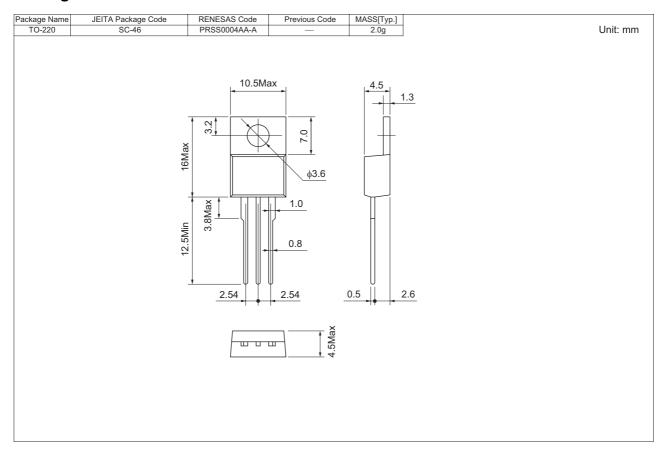








# **Package Dimensions**



# **Order Code**

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name	BCR20AM-12LB
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	BCR20AM-12LB-A8

Note: Please confirm the specification about the shipping in detail.

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